

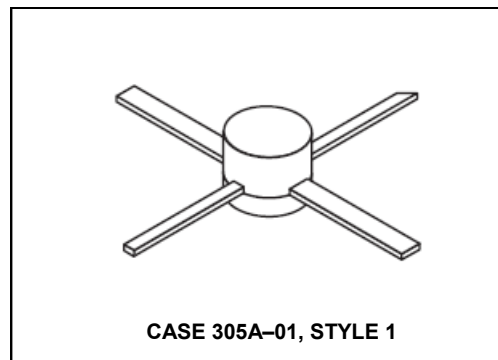
The RF Line NPN Silicon High-Frequency Transistor 1.0W, 400MHz, 28V

Rev. V1

Designed for wideband amplifier, driver or oscillator applications in military, mobile, and aircraft radio.

- Specified 28 V, 400 MHz characteristics —
Output power = 1.0 W
Power gain = 15 dB min.
Efficiency = 45% typ.
- Emitter ballast and low current density for improved MTBF
- Common emitter for improved stability

Product Image



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	30	Vdc
Collector–Base Voltage	V_{CBO}	40	Vdc
Emitter–Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	150	mAdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	6.1 35	Watts mW/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	28.5	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector–Emitter Breakdown Voltage ($I_C = 5.0 \text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	35	—	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 0.1 \text{ mAdc}$, $I_E = 0$)	$V_{(BR)CBO}$	35	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 1.0 \text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	—	Vdc
Collector Cutoff Current ($V_{CE} = 20 \text{ Vdc}$, $I_B = 0$)	I_{CEO}	—	—	1.0	mAdc

(continued)

The RF Line NPN Silicon High-Frequency Transistor
1.0W, 400MHz, 28V

Rev. V1

ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

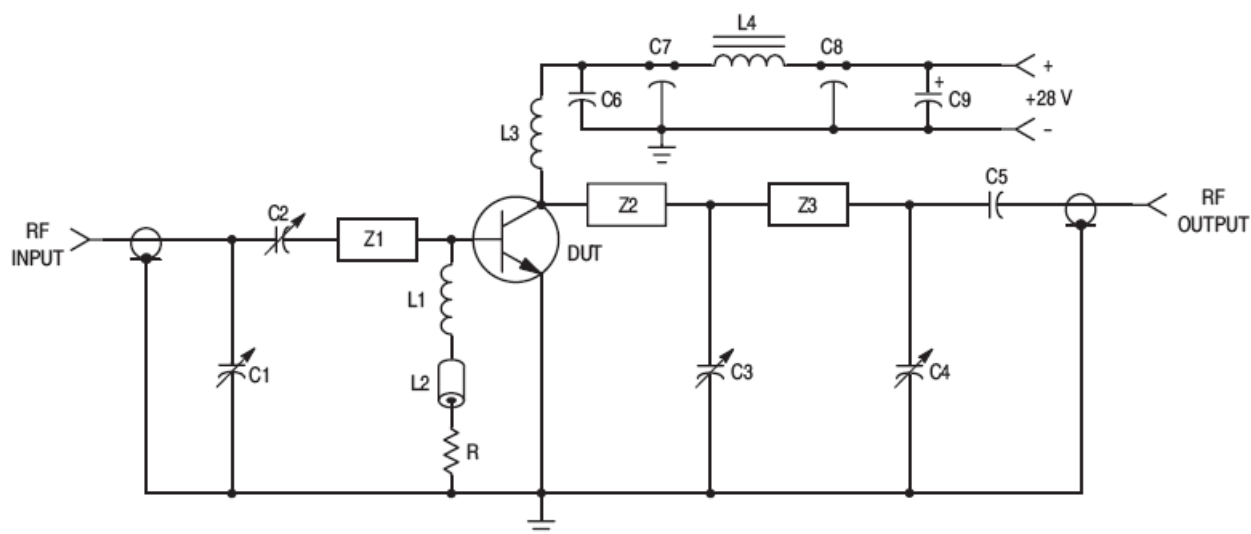
Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
DC Current Gain ($I_C = 100 \text{ mA dc}$, $V_{CE} = 10 \text{ V dc}$)	h_{FE}	20	60	150	—
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product ($I_C = 100 \text{ mA dc}$, $V_{CE} = 20 \text{ V dc}$, $f = 200 \text{ MHz}$)	f_T	—	2.5	—	GHz
Output Capacitance ($V_{CB} = 28 \text{ V dc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C_{ob}	—	3.5	5.0	pF
FUNCTIONAL TESTS					
Common–Emitter Amplifier Power Gain (1) ($V_{CC} = 28 \text{ V dc}$, $P_{out} = 1.0 \text{ W}$, $f = 400 \text{ MHz}$)	G_{pe}	15	16	—	dB
Collector Efficiency ($V_{CC} = 28 \text{ V dc}$, $P_{out} = 1.0 \text{ W}$, $f = 400 \text{ MHz}$)	η	—	45	—	%
Series Equivalent Input Impedance ($V_{CC} = 28 \text{ V dc}$, $P_{out} = 1.0 \text{ W}$, $f = 400 \text{ MHz}$)	Z_{in}	—	$6.4 - j4.8$	—	Ohms
Series Equivalent Output Impedance ($V_{CC} = 28 \text{ V dc}$, $P_{out} = 1.0 \text{ W}$, $f = 400 \text{ MHz}$)	Z_{out}	—	$75 - j45$	—	Ohms

NOTE:

- Class C

The RF Line NPN Silicon High-Frequency Transistor 1.0W, 400MHz, 28V

Rev. V1



C1, C2, C4 — 1.0–20 pF JOHANSON 9063
 C3 — 1.0–10 pF JOHANSON
 C5 — 150 pF Chip
 C6 — 0.1 μ F
 C7, C8 — 680 pF Feedthru
 C9 — 1.0 μ F TANTALUM

L1, L3 — 5 Turns, AWG #20, 1/4" I.D.
 L2 — Ferrite Bead, FERROXCUBE
 No. 56–590–65/4B
 L4 — FERROXCUBE VK200–20/4B
 Input/Output Connectors — Type N
 Board — Glass Teflon, $\epsilon = 2.56$, $t = 0.062$ "

R — 4.7 Ohms, 1/4 W
 Z1 — 2.0" x 0.1" MICROSTRIP LINE
 Z2, Z3 — 2.6" x 0.1" MICROSTRIP LINE

Figure 1. 400 MHz Power Gain Test Circuit

PACKAGE DIMENSIONS

